

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for forming a pattern comprising the steps of:
forming a first region and a second region;
discharging a composition containing a pattern formation material to a region across the second region and the first region; and
flowing a part of the composition discharged to the first region into the second region to form a conductive layer;
wherein wettability of the first region with respect to the composition is lower than wettability of the second region with respect to the composition.

2. (Currently Amended) A method for forming a pattern comprising the steps of:
forming selectively a mask over a substrate;
forming a first region by using the mask;
forming a second region by removing the mask;
discharging a composition containing a pattern formation material to a region across the second region and the first region; and
flowing a part of the composition discharged to the first region into the second region to form a conductive layer;
wherein wettability of the first region with respect to the composition is lower than wettability of the second region with respect to the composition.

3. (Withdrawn) A method for forming a pattern comprising the steps of:
forming selectively a photocatalytic substance over a substrate;
forming a first region over the substrate and the photocatalytic substance;
emitting light to the photocatalytic substance to form a second region;
discharging a composition containing a pattern formation material to a region across the second region and the first region; and
flowing a part of the composition discharged to the first region into the second region;

wherein wettability of the first region with respect to the composition is lower than wettability of the second region with respect to the composition.

4. (Withdrawn) A method for forming a pattern comprising the steps of:
forming a first region over a substrate;
emitting light selectively to the first region to form a second region;
discharging a composition containing a pattern formation material to a region across the second region and the first region; and
flowing a part of the composition discharged to the first region into the second region;
wherein wettability of the first region with respect to the composition is lower than wettability of the second region with respect to the composition.

5. (Currently Amended) The method for forming the pattern according to ~~any one of Claims 1 to 4~~ claim 1 or 2, wherein a the first region is formed by forming a substance having a fluorocarbon chain.

6. (Withdrawn) The method for forming the pattern according to Claim 3, wherein the photocatalytic substance is formed by using titanium oxide.

7. (Withdrawn) A method for manufacturing a thin film transistor comprising the steps of:
forming a first region and a second region;
discharging a composition containing a conductive material to a region across the second region and the first region; and
flowing a part of the composition discharged to the first region into the second region to form an electrode layer;
wherein wettability of the first region with respect to the composition is lower than wettability of the second region with respect to the composition.

8. (Withdrawn) A method for manufacturing a thin film transistor comprising the steps of:

forming a first region and a second region;
discharging a composition containing a first conductive material to a region across the first region and the second region;
flowing a part of the composition discharged to the first region into the second region to form an electrode layer; and
discharging a second conductive material to the second region to be in contact with the electrode layer to form a wiring layer;
wherein wettability of the first region with respect to the composition is lower than wettability of the second region with respect to the composition.

9. (Withdrawn) A method for forming a pattern comprising the steps of:
forming selectively a photocatalytic substance over a substrate;
forming a first region over the substrate and the photocatalytic substance;
emitting light to the photocatalytic substance to form a second region;
discharging a composition containing a conductive material to a region across the first region and the second region; and
flowing a part of the composition discharged to the first region into the second region to form an electrode layer;
wherein wettability of the first region with respect to the composition is lower than wettability of the second region with respect to the composition.

10. (Withdrawn) The method for manufacturing the thin film transistor according to any one of Claims 7 to 9, wherein the first region is formed by forming a substance having a fluorocarbon chain.

11. (Withdrawn) The method for manufacturing the thin film transistor according to Claim 9, wherein titanium oxide is formed as the photocatalytic substance.

12. (Withdrawn) A method for manufacturing a display device using the thin film transistor manufactured by the method according to Claim 7 or 9, wherein the electrode layer is formed as a gate electrode layer.

13. (Withdrawn) A method for manufacturing a display device using the thin film transistor manufactured by the method according to Claim 8, wherein the electrode layer is formed as a gate electrode layer and the wiring layer is formed as a gate wiring layer.

14. (Withdrawn) A method for manufacturing a thin film transistor comprising the steps of:

forming a first region and a second region over a substrate;

discharging a composition containing a mask formation material to a region across the first region and the second region;

flowing a part of the composition containing the mask formation material discharged to the first region into the second region to form a mask;

changing a part of the first region by using the mask to form a third region;

forming a fourth region by removing the mask;

discharging a composition containing a conductive material to a region across the third region and the fourth region; and

flowing the composition in the fourth region into the third region to form a first electrode layer and a second electrode layer;

wherein wettability of the first region with respect to the composition containing the mask formation material is lower wettability than that of the second region with respect to the composition containing the mask formation material, and wettability of the fourth region with respect to the conductive material is lower than wettability of the third region with respect to the conductive material.

15. (Withdrawn) The method for manufacturing the thin film transistor according to Claim 14, wherein the first region is formed by forming a substance having fluorocarbon.

16. (Withdrawn) A method for manufacturing a display device using the thin film transistor manufactured by the method according to Claim 12, wherein each of the first electrode layer and the second electrode layer is formed as a source electrode layer or a drain electrode layer.

17. (Withdrawn) A thin film transistor comprising:
a wiring layer provided over a substrate; and
an electrode layer being in contact with the wiring layer;
wherein the wiring layer is formed on a first region, the electrode layer is formed on a second region, and wettability of the second region with respect to the electrode layer and the wiring layer is lower than wettability with respect to the electrode layer and the wiring layer of the first region.

18. (Withdrawn) The thin film transistor according to Claim 17,
wherein the electrode layer has a smaller width and a thinner thickness than those of the wiring layer.

19. (Withdrawn) A display device comprising:
a wiring layer provided over a substrate; and
an electrode layer being in contact with the wiring layer;
wherein the wiring layer is formed on a first region, the electrode layer is formed on a second region, and wettability of the second region with respect to the electrode layer and the wiring layer is lower than wettability of the first region with respect to the electrode layer and the wiring layer.

20. (Withdrawn) The display device according to Claim 19,
wherein the electrode layer has a smaller width and a thinner thickness than those of the wiring layer.

21. (Withdrawn) A television device comprising:
a wiring layer provided over a substrate; and
an electrode layer being in contact with the wiring layer;
wherein the wiring layer is formed on a first region, the electrode layer is formed on a second region, and wettability of the second region with respect to the electrode layer and the

wiring layer is lower than wettability of the first region with respect to the electrode layer and the wiring layer.

22. (Withdrawn) The television device according to Claim 21,
wherein the electrode layer has a smaller width and a thinner thickness than those of the
wiring layer.

23. (New) The method for forming the pattern according to claim 1, wherein the method
further comprises a step of removing a pattern in the second region after the step of flowing the
part of the composition.

24. (New) The method for forming the pattern according to claim 1, wherein the method
further comprises a step of discharging a second composition containing a second pattern
formation material over a pattern in the second region to form a wide width pattern after the step
of flowing the part of the composition.

25. (New) The method for forming the pattern according to claim 2, wherein the method
further comprises a step of removing a pattern in the second region after the step of flowing the
part of the composition.

26. (New) The method for forming the pattern according to claim 2, wherein the method
further comprises a step of discharging a second composition containing a second pattern
formation material over a pattern in the second region to form a wide width pattern after the step
of flowing the part of the composition.

27. (New) A method for forming a pattern comprising the steps of:
forming a first region and a second region;
discharging a composition containing a pattern formation material to a region across the
second region and the first region; and
flowing a part of the composition discharged to the first region into the second region;

wherein a contact angle of the first region to the composition containing the pattern formation material is larger than the contact angle of the second region to the composition containing the pattern formation material by 30° or more.

28. (New) The method for forming the pattern according to claim 27, wherein the first region is formed by forming a substance having a fluorocarbon chain.

29. (New) The method for forming the pattern according to claim 27, wherein the method further comprises a step of removing a pattern in the second region after the step of flowing the part of the composition.

30. (New) The method for forming the pattern according to claim 27, wherein the method further comprises a step of discharging a second composition containing a second pattern formation material over a pattern in the second region to form a wide width pattern after the step of flowing the part of the composition.

31. (New) A method for forming a pattern comprising the steps of:
forming selectively a mask over a substrate;
forming a first region by using the mask;
forming a second region by removing the mask;
discharging a composition containing a pattern formation material to a region across the second region and the first region; and
flowing a part of the composition discharged to the first region into the second region;
wherein a contact angle of the first region to the composition containing the pattern formation material is larger than the contact angle of the second region to the composition containing the pattern formation material by 30° or more.

32. (New) The method for forming the pattern according to claim 31, wherein the first region is formed by forming a substance having a fluorocarbon chain.

33. (New) The method for forming the pattern according to claim 31, wherein the method further comprises a step of removing a pattern in the second region after the step of flowing the part of the composition.

34. (New) The method for forming the pattern according to claim 31, wherein the method further comprises a step of discharging a second composition containing a second pattern formation material over a pattern in the second region to form a wide width pattern after the step of flowing the part of the composition.